

BFR30LT1, BFR31LT1

JFET Amplifiers

N-Channel

Features

- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain – Source Voltage	V_{DS}	25	Vdc
Gate – Source Voltage	V_{GS}	25	Vdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

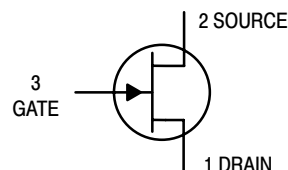
Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- Device mounted on FR4 glass epoxy printed circuit board using the recommended footprint.
- Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

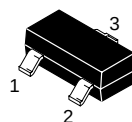


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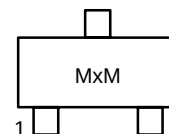
<http://onsemi.com>



MARKING DIAGRAM



SOT-23
CASE 318
STYLE 10



x = 1 or 2
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
BFR30LT1	SOT-23	3000/Tape & Reel
BFR30LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
BFR31LT1	SOT-23	3000/Tape & Reel
BFR31LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Gate Reverse Current ($V_{GS} = 10\text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	–	0.2	nAdc
Gate Source Cutoff Voltage ($I_D = 0.5\text{ nAdc}$, $V_{DS} = 10\text{ Vdc}$)	$V_{GS(OFF)}$	–	5.0	Vdc
Gate Source Voltage ($I_D = 1.0\text{ mAdc}$, $V_{DS} = 10\text{ Vdc}$)	V_{GS}	–0.7	–3.0	Vdc
		–	–1.3	
($I_D = 50\text{ }\mu\text{Adc}$, $V_{DS} = 10\text{ Vdc}$)		–	–4.0	
		–	–2.0	

ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current ($V_{DS} = 10\text{ Vdc}$, $V_{GS} = 0$)	I_{DSS}	4.0	10	mAdc
		1.0	5.0	

SMALL-SIGNAL CHARACTERISTICS

Forward Transconductance ($I_D = 1.0\text{ mAdc}$, $V_{DS} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	$ y_{fs} $	1.0	4.0	mmhos
		1.5	4.5	
($I_D = 200\text{ }\mu\text{Adc}$, $V_{DS} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)		0.5	–	
		0.75	–	
Output Admittance ($I_D = 1.0\text{ mAdc}$, $V_{DS} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	$ y_{os} $	40	25	μmhos
($I_D = 200\text{ }\mu\text{Adc}$, $V_{DS} = 10\text{ Vdc}$)		20	15	
Input Capacitance ($I_D = 1.0\text{ mAdc}$, $V_{DS} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{iss}	–	5.0	pF
($I_D = 200\text{ }\mu\text{Adc}$, $V_{DS} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)		–	4.0	
Reverse Transfer Capacitance ($I_D = 1.0\text{ mAdc}$, $V_{DS} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{rss}	–	1.5	pF
($I_D = 200\text{ }\mu\text{Adc}$, $V_{DS} = 10\text{ Vdc}$, $f = 1.0\text{ MHz}$)		–	1.5	

TYPICAL CHARACTERISTICS

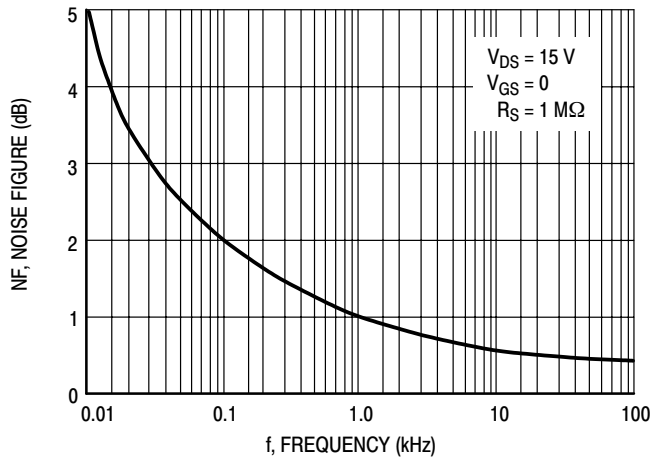


Figure 1. Noise Figure versus Frequency

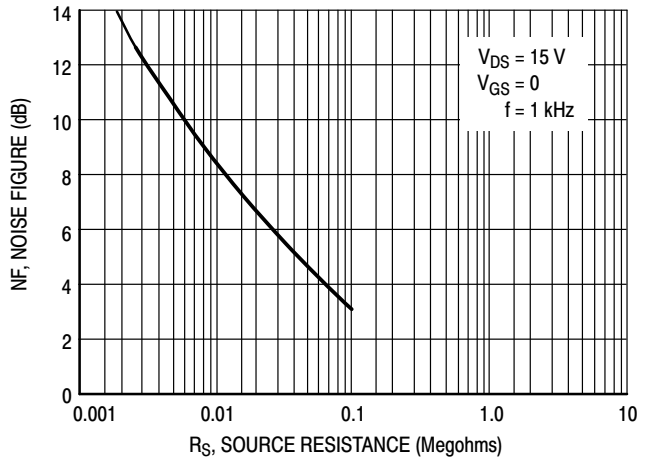


Figure 2. Noise Figure versus Source Resistance

TYPICAL CHARACTERISTICS

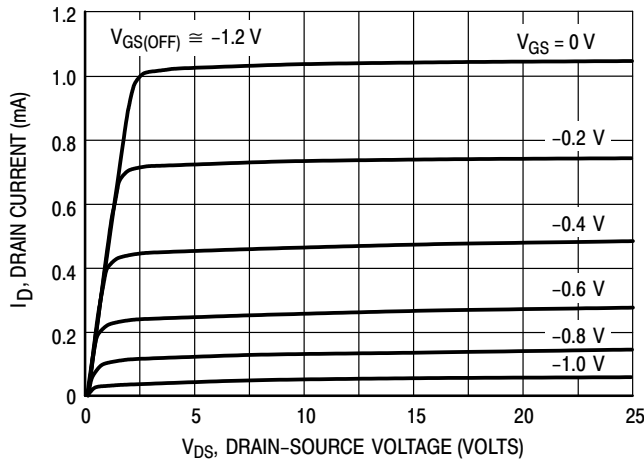


Figure 3. Typical Drain Characteristics

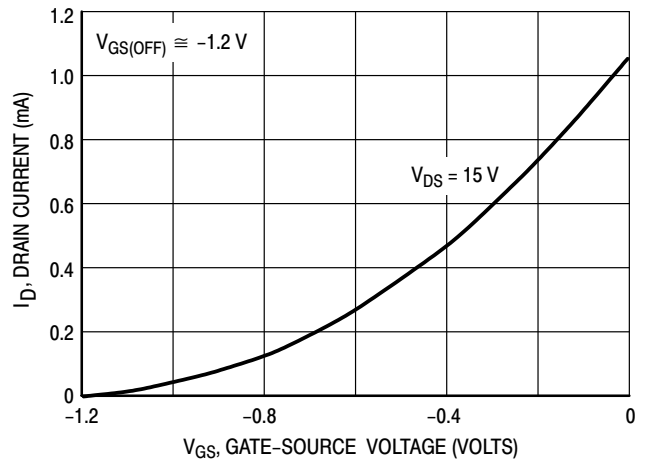


Figure 4. Common Source Transfer Characteristics

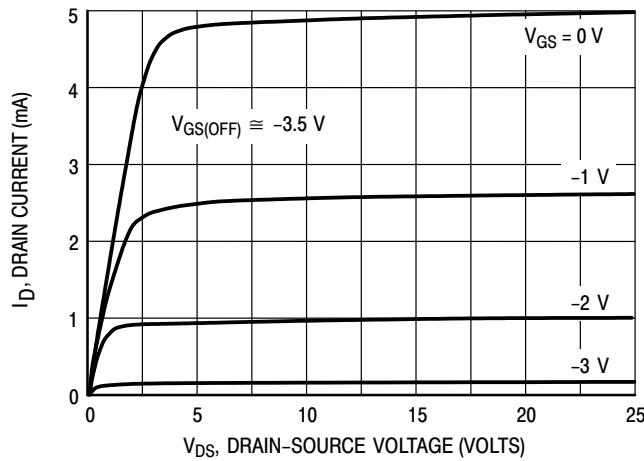


Figure 5. Typical Drain Characteristics

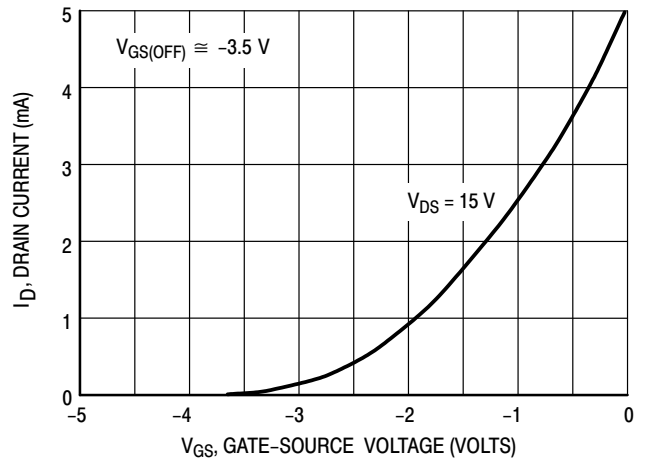


Figure 6. Common Source Transfer Characteristics

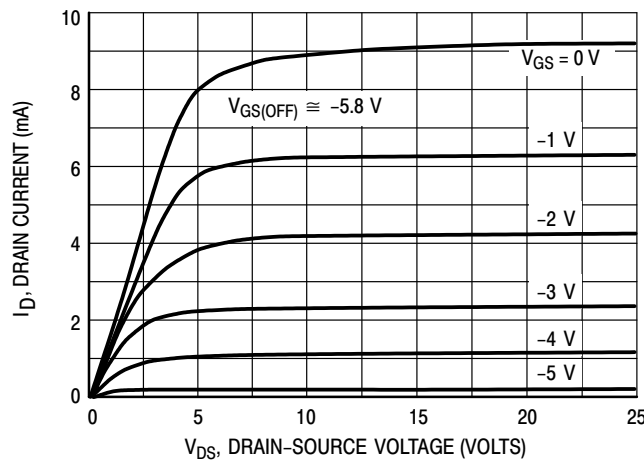


Figure 7. Typical Drain Characteristics

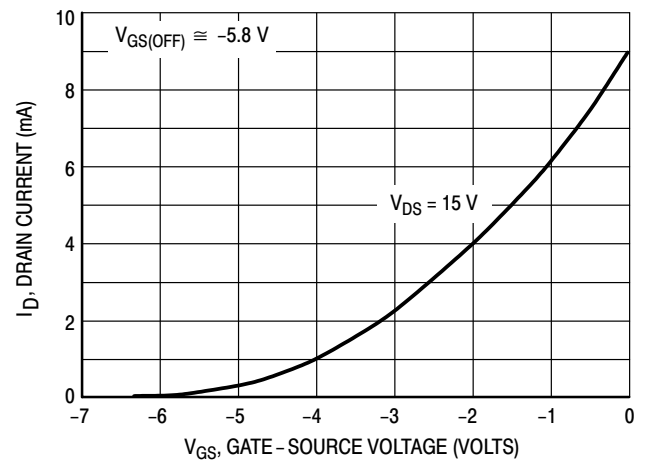


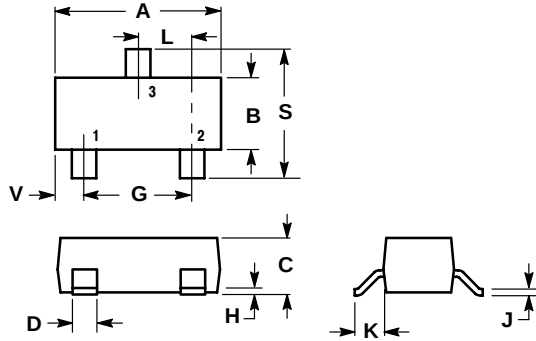
Figure 8. Common Source Transfer Characteristics

Note: Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%). Under dc conditions, self heating in higher I_{DSS} units reduces I_{DSS} .

BFR30LT1, BFR31LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AK



NOTES:

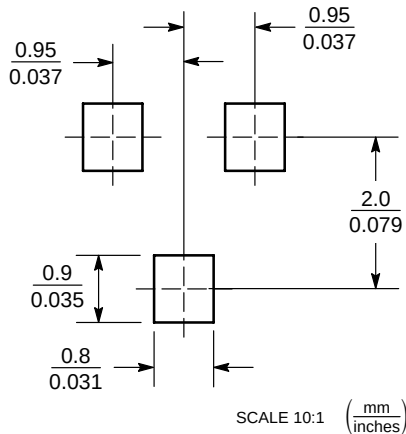
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 10:

1. DRAIN
2. SOURCE
3. GATE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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